| L Number | Hits   | Search Text  | DB                                       | Time stamp         |
|----------|--------|--|--|--------------------|
| 1        | 1175   |  | USPAT;                                   | 2002/12/08 12:17   |
|          | 11/3   | dop\$3 and crystalliz\$5   | EPO; JPO;                                | 2002/12/08 12:17   |
|          |        | dop\$3 and crystarriz\$3   | 1  |                    |
| _        | 34     |  | DERWENT                                  | 2002/12/00 12:12   |
| 2        | 34     | <b>↑</b> *** * * * * * * * * * * * * * * * * *                             | USPAT;                                   | 2002/12/08 12:12   |
|          |        | dop\$3 same crystalliz\$5  | EPO; JPO;                                |                    |
| _        |        |  | DERWENT                                  |                    |
| 3        | 12     |  | USPAT;                                   | 2002/12/08 12:12   |
|          |        | dop\$3 same crystalliz\$5) same gate                                       | EPO; JPO;                                |                    |
|          | •      |  | DERWENT                                  |                    |
| 4        | 350    | radiat\$3 and amorphous and silicon and                                    | USPAT;                                   | 2002/12/08 12:22   |
|          |        | dop\$3 and crystalliz\$5 and (gate with                                    | EPO; JPO;                                |                    |
| -        | +      | dop\$3)  | DERWENT                                  |                    |
| 5        | 315    |  | USPAT;                                   | 2002/12/08 12:20   |
|          |        | dop\$3 and crystalliz\$5 and (gate with                                    | EPO; JPO;                                |                    |
|          |        | dop\$3)) and laser   | DERWENT                                  |                    |
| 6        | 181    | ((radiat\$3 and amorphous and silicon and                                  | USPAT;                                   | 2002/12/08 12:21   |
| Ĭ        | 101    | dop\$3 and crystalliz\$5 and (gate with                                    | EPO; JPO;                                | 2002/12/00 12:21   |
|          |        |  |  |                    |
| _        | 101    | dop\$3)) and laser) and 438/\$3.ccls.                                      | DERWENT                                  | 0000/10/00 10 01   |
| 7        | 181    | (((radiat\$3 and amorphous and silicon and                                 | USPAT;                                   | 2002/12/08 12:21   |
|          |        | dop\$3 and crystalliz\$5 and (gate with                                    | EPO; JPO;                                |                    |
|          |        | dop\$3)) and laser) and 438/\$3.ccls.) and                                 | DERWENT                                  |                    |
| İ        | ĺ      | @ad<20010829   |  |                    |
| 8        | 33     | radiat\$3 and amorphous and silicon and                                    | USPAT;                                   | 2002/12/08 12:59   |
|          |        | dop\$3 and crystalliz\$5 and (gate with                                    | EPO; JPO;                                |                    |
|          |        | dop\$3 with amorphous)   | DERWENT                                  |                    |
| 9        | 4      |  | USPAT;                                   | 2002/12/08 13:04   |
|          |        | dop\$3 with amorphous)   | EPO; JPO;                                |                    |
|          |        |  | DERWENT                                  | :                  |
| 10       | 2      | radiat\$3 same amorphous same (crystalliz\$5                               | USPAT;                                   | 2002/12/08 13:08   |
| 10       | -      | with gate with dop\$3)   | EPO; JPO;                                | 2002/12/00 13:00   |
| ĺ        |        | with gate with dopps,  | DERWENT                                  |                    |
| 11       | 11     | radiat\$3 same amorphous same crystalliz\$5                                |  | 2002/12/08 13:30   |
| 11       | 1      |  | USPAT;                                   | 2002/12/08 13:30   |
|          |        | same (gate with dop\$3)  | EPO; JPO;                                |                    |
| 1.0      |        | 100  | DERWENT                                  | 2000 (10 (00 15 51 |
| 12       | 28     | anneal\$3 same crystalliz\$5 same (amorphous                               | USPAT;                                   | 2002/12/08 15:51   |
| ĺ        | ĺ      | with gate with dop\$3)   | EPO; JPO;                                |                    |
|          |        |  | DERWENT                                  | 1                  |
| 13       | 3      | ("5872761"   "5994179"   "6054355").PN.                                    | USPAT                                    | 2002/12/08 14:00   |
| 14       | 11     | gate with height with "500" with   | USPAT;                                   | 2002/12/08 15:55   |
|          |        | (nanometer\$1 or nm)   | EPO; JPO;                                |                    |
|          |        |  | DERWENT                                  |                    |
| 15       | 62     | gate with height with ("400" or "300" or                                   | USPAT;                                   | 2002/12/08 15:56   |
|          |        | "200" or "100") with (nanometer\$1 or nm)                                  | EPO; JPO;                                |                    |
|          |        |  | DERWENT                                  |                    |
| _        | 213204 | 257/\$3.ccls. or 438/\$3.ccls.   | USPAT;                                   | 2002/12/08 11:42   |
|          |        |  | EPO; JPO;                                |                    |
|          |        |  | DERWENT                                  |                    |
| _        | 6      | (257/\$3.ccls. or 438/\$3.ccls.) and                                       | USPAT;                                   | 2002/04/09 09:46   |
|          |        | insulat\$3 and radiat\$3 and (amorphous                                    | EPO; JPO;                                | 2002/04/05 09.40   |
|          |        | near2 silicon) and crystall\$7 and   | DERWENT                                  | 1                  |
|          |        |  | DEVMENT                                  | 1                  |
|          | ,      | explosive  | HODAM                                    | 2002/04/00 00 50   |
| -        | 1      | ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' '                                      | USPAT;                                   | 2002/04/09 09:58   |
|          |        | (explosive adj recrystallization)) and                                     | EPO; JPO;                                |                    |
|          |        | irradiat\$3 and dopant and gate  | DERWENT                                  | 1                  |
|          | 103    |  | USPAT;                                   | 2002/04/09 09:59   |
|          |        | recrystallization and irradiat\$3 and                                      | EPO; JPO;                                |                    |
|          |        | dopant and gate  | DERWENT                                  |                    |
| -        | 85     | ((257/\$3.ccls. or 438/\$3.ccls.) and                                      | USPAT;                                   | 2002/04/09 15:19   |
| !        |        | recrystallization and irradiat\$3 and                                      | EPO; JPO;                                | 1                  |
|          | 1      | dopant and gate) and (amorphous adj  | DERWENT                                  |                    |
|          |        | silicon)   |  |                    |
|          | 3      | mosfet same (laser or irradiate) same                                      | USPAT;                                   | 2002/04/09 16:11   |
| . – '    | 1      | amorphous same (dopant or dope)  | EPO; JPO;                                | -552, 51, 55 15.11 |
| -        | I      | (doparte of dope)  | 1  | 1                  |
| _        |        |  |  |                    |
| _        | 111    | (lagar or irradiata) came (amorphous adi                                   | DERWENT                                  | 2002/04/10 16:52   |
| -<br>-   | 111    | (laser or irradiate) same (amorphous adj                                   | USPAT;                                   | 2002/04/10 16:52   |
| -        | 111    | (laser or irradiate) same (amorphous adj<br>silicon) same (dopant or dope) | USPAT;<br>EPO; JPO;                      | 2002/04/10 16:52   |
| -        |        | silicon) same (dopant or dope)   | USPAT;<br>EPO; JPO;<br>DERWENT           |                    |
| -        | 111    | silicon) same (dopant or dope) ((laser or irradiate) same (amorphous adj   | USPAT;<br>EPO; JPO;<br>DERWENT<br>USPAT; | 2002/04/10 16:52   |
| -        |        | silicon) same (dopant or dope)   | USPAT;<br>EPO; JPO;<br>DERWENT           |                    |

| - | 241      | mosfet with laser  | USPAT;               | 2002/04/09 17:50   |
|---|----------|--|----------------------|--------------------|
|   |          |  | EPO; JPO;            |                    |
|   |          |  | DERWENT              | 0000/04/00 17 70   |
| - | 2        | (mosfet with laser) same (amorphous adj                                      | USPAT;<br>EPO; JPO;  | 2002/04/09 17:52   |
|   |          | SITICON  | DERWENT              |                    |
| _ | 12       | (mosfet with laser) same (dope dopant  | USPAT;               | 2002/04/09 18:06   |
|   | 12       | doped)   | EPO; JPO;            | 2002/04/03 10:00   |
|   |          |  | DERWENT              |                    |
| - | 42       | (mosfet with laser) and ((dope dopant  | USPAT;               | 2002/04/09 18:07   |
|   |          | doped) with gate)  | EPO; JPO;            |                    |
|   |          |  | DERWENT              |                    |
| - | 12557    | (mosfet or fet or mos) same dop\$3 same                                      | USPAT;               | 2002/04/10 17:18   |
|   |          | gate   | EPO; JPO;            |                    |
|   | 158      | //mosfot or fot or most same done?   | DERWENT              | 2002/04/10 11:07   |
| - | 136      | ((mosfet or fet or mos) same dop\$3 same gate) same (laser or irradiation)   | USPAT;<br>EPO; JPO;  | 2002/04/10 11:0/   |
|   |          | gate/ Same (lasel of filadiacion)  | DERWENT              |                    |
| _ | 4        | "5966605"  | USPAT;               | 2002/04/10 11:07   |
|   | _        |  | EPO; JPO;            |                    |
|   |          |  | DERWENT              |                    |
| - | 54793    | gate with silicon  | USPAT;               | 2002/04/10 14:12   |
|   |          |  | EPO; JPO;            |                    |
|   | _        |  | DERWENT              |                    |
| - | 6957     | ((mosfet or fet or mos) same dop\$3 same                                     | USPAT;               | 2002/04/10 14:12   |
|   |          | gate) and (gate with silicon)  | EPO; JPO;            |                    |
| _ | 15744    | gato noar? silicon   | DERWENT              | 2002/04/10 14:12   |
| - | 15/44    | gate near2 silicon   | USPAT;<br>EPO; JPO;  | 2002/04/10 14:12   |
|   |          |  | DERWENT              |                    |
| - | 2731     | ((mosfet or fet or mos) same dop\$3 same                                     | USPAT;               | 2002/04/10 14:12   |
|   |          | gate) and (gate near2 silicon)   | EPO; JPO;            | ,,                 |
|   |          |  | DERWENT              |                    |
| - | 234      | (((mosfet or fet or mos) same dop\$3 same                                    | USPAT;               | 2002/04/10 14:15   |
|   |          | gate) and (gate near2 silicon)) and (laser                                   | EPO; JPO;            |                    |
|   |          | or irradiate)  | DERWENT              | 0000 40 1 12 5 1 5 |
| - | 110      | ((((mosfet or fet or mos) same dop\$3 same                                   | USPAT;               | 2002/04/10 16:15   |
|   |          | gate) and (gate near2 silicon)) and (laser                                   | EPO; JPO;            |                    |
|   |          | or irradiate)) and amorphous and (recrystallize or polycrystalline or        | DERWENT              |                    |
|   |          | crystalline)   |                      |                    |
| - | 13       | "5937325"  | USPAT;               | 2002/04/10 16:19   |
|   |          |  | EPO; JPO;            | =                  |
|   |          |  | DERWENT              |                    |
| - | 8        | "6013928"  | USPAT;               | 2002/04/10 16:20   |
|   |          |  | EPO; JPO;            |                    |
|   |          | (1)  | DERWENT              | 2000/04/10 15 52   |
| - | 34       |  | USPAT;               | 2002/04/10 16:53   |
|   |          | silicon) same ((dopant or dope) and (sputter or deposition or evaporation))  | EPO; JPO;<br>DERWENT |                    |
| _ | 3488     | (mosfet or fet or mos) same dop\$3 same                                      | USPAT;               | 2002/04/10 17:20   |
|   | 3,00     | qate same (sputter or evaporat\$3 or   | EPO; JPO;            | 2002,04,10 17.20   |
|   |          | deposit\$3)  | DERWENT              |                    |
| - | 3958     | ((mosfet or fet or mos) same dop\$3 same                                     | USPAT;               | 2002/04/10 17:21   |
|   |          | gate) and (dop\$3 with (sputter or   | EPO; JPO;            |                    |
|   |          | deposit\$3 or evaporat\$3))  | DERWENT              |                    |
| - | 137      | ((mosfet or fet or mos) same dop\$3 same                                     | USPAT;               | 2002/04/10 17:21   |
| } |          | gate) and (dop\$3 with (sputter or   | EPO; JPO;            |                    |
| _ | / A 1    | evaporat\$3))  | DERWENT<br>USPAT;    | 2002/04/10 17:25   |
| - | 41       | ((mosfet or fet or mos) same dop\$3 same gate) same (dop\$3 with (sputter or | EPO; JPO;            | 2002/04/10 1/:23   |
|   |          | evaporat\$3))  | DERWENT              |                    |
| _ | 75       | ((mosfet or fet or mos) same dop\$3 same                                     | USPAT;               | 2002/04/10 17:32   |
|   |          | gate) same (dop\$3 with (sputter\$3 or                                       | EPO; JPO;            |                    |
| 1 |          | evaporat\$3))  | DERWENT              |                    |
| - | 320      | (dop\$3 with (sputter\$3 or evaporat\$3) with                                | USPAT;               | 2002/04/10 17:46   |
|   | ļ        | silicon) and (mos or fet or mosfet)  | EPO; JPO;            |                    |
|   | 1        |  | DERWENT              |                    |
| - | 35       | (dop\$3 with (sputter\$3 or evaporat\$3) with                                | USPAT;               | 2002/04/10 17:35   |
| 1 |          | silicon) same (mos or fet or mosfet)   | EPO; JPO;            |                    |
|   | <u> </u> |  | DERWENT              |                    |

| - | 28    | (dop\$3 with (sputter\$3 or evaporat\$3) with | USPAT;    | 2002/04/10 17:51   |
|---|-------|---|-----------|--------------------|
|   |       | silicon) same laser                           | EPO; JPO; |                    |
|   |       |   | DERWENT   |                    |
| - | 190   | (dop\$3 with (sputter\$3 or evaporat\$3))     | USPAT;    | 2002/04/10 18:02   |
|   | i     | same laser                                    | EPO; JPO; |                    |
|   |       |   | DERWENT   |                    |
| - | 2     | "6165875"                                     | USPAT;    | 2002/04/10 18:02   |
|   |       |   | EPO; JPO; |                    |
|   |       |   | DERWENT   |                    |
| _ | 2848  | gate with (metal or cap or capped) with       | USPAT;    | 2002/04/11 16:14   |
|   |       | (tungsten or tantalum or titanium or          | EPO; JPO; |                    |
|   |       | platinum)                                     | DERWENT   |                    |
| _ | 331   | (gate with (metal or cap or capped) with      | USPAT;    | 2002/04/11 16:20   |
|   |       | (tungsten or tantalum or titanium or          | EPO; JPO; |                    |
|   |       | platinum) ) and laser                         | DERWENT   |                    |
| _ | 89    | (gate with (metal or cap or capped) with      | USPAT;    | 2002/04/11 16:20   |
|   |       | (tungsten or tantalum or titanium or          | EPO; JPO; | 2002, 01, 11 10.20 |
|   |       | platinum) ) and laser and mosfet              | DERWENT   |                    |
| _ | 4     | "6077758"                                     | USPAT;    | 2002/04/11 17:34   |
|   | 1     | 0077730                                       | JPO;      | 2002/04/11 17.54   |
|   |       |   | DERWENT   |                    |
| _ | 11867 | (boron or indium or arsenic or phosphorus)    | USPAT;    | 2002/04/15 14:06   |
| _ | 1100/ | with (sputter\$3 or CVD or evaporat\$3)       | EPO; JPO; | 2002/04/13 14:00   |
|   | į     | with (sputters) of CVD of evaporates)         | DERWENT   |                    |
|   | 12    | //>   |           | 2002/04/15 14:02   |
| _ | 1 12  | ((boron or indium or arsenic or               | USPAT;    | 2002/04/15 14:02   |
|   |       | phosphorus) with (sputter\$3 or CVD or        | EPO; JPO; |                    |
|   | 1000  | evaporat\$3)) same dopant same laser          | DERWENT   | 0000/01/15 15 10   |
| - | 1098  | ((boron or indium or arsenic or               | USPAT;    | 2002/04/15 15:10   |
|   |       | phosphorus) near2 layer) with (sputter\$3     | EPO; JPO; |                    |
|   |       | or CVD or evaporat\$3)                        | DERWENT   |                    |
| - | 33    |   | USPAT;    | 2002/04/15 14:09   |
|   |       | phosphorus) near2 layer) with (sputter\$3     | EPO; JPO; |                    |
|   |       | or CVD or evaporat\$3)) same dopant           | DERWENT   |                    |
| - | 239   |   | USPAT;    | 2002/04/15 15:13   |
|   |       | phosphorus) near2 layer) with (sputter\$3     | EPO; JPO; |                    |
|   |       | or CVD or evaporat\$3) with surface           | DERWENT   |                    |
| - | 46    |   | USPAT;    | 2002/04/15 15:14   |
|   |       | phosphorus) near2 layer) with (sputter\$3     | EPO; JPO; |                    |
|   | :     | or CVD or evaporat\$3) with surface) and      | DERWENT   |                    |
|   |       | laser   |           |                    |
| - | 2     | 5966605.pn.                                   | USPAT;    | 2002/09/13 13:14   |
|   |       |   | EPO; JPO; |                    |
|   |       |   | DERWENT   |                    |
| - | 2     | 6365476.pn.                                   | USPAT;    | 2002/09/13 13:15   |
|   |       |   | EPO; JPO; |                    |
|   |       |   | DERWENT   |                    |
| - | 2     | 6274488.pn.                                   | USPAT;    | 2002/09/13 13:16   |
|   |       | _   | EPO; JPO; |                    |
|   | 1     |   | DERWENT   |                    |
| _ | 2     | 6077758.pn.                                   | USPAT;    | 2002/09/13 13:16   |
|   |       | •   | EPO; JPO; |                    |
|   |       |   | DERWENT   |                    |
|   | 1     | I   |           | 1                  |